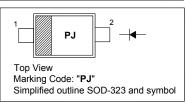
HIGH-SPEED SWITCHING DIODE

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Absolute Maximum Rutings (1a = 25 °C)			
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V _R	75	V
Continuous Forward Current	I _F	125	mA
Repetitive Peak Forward Current	I _{FRM}	450	mA
Non-repetitive Peak Forward Current $T_j = 25 ^{\circ}\text{C}$, at $t = 1 ^{\circ}\text{L}$	JS S	4	
at t = 1 r	mS I _{FSM}	1	Α
at t = 1 5	6	0.5	
Power Dissipation	P _{tot}	250	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	- 65 to + 150	°C

Characteristics at T_a = 25 °C

α			
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V _F	715 855 1 1.25	mV mV V
Reverse Current at V_R = 25 V at V_R = 75 V at V_R = 25 V, T_j = 150 °C at V_R = 75 V, T_j = 150 °C	I _R	30 1 30 50	nΑ μΑ μΑ μΑ
Diode Capacitance at f = 1 MHz	C _d	2	pF
Reverse Recovery Time at I_F = 10 mA, I_R = 10 mA, R_L = 100 Ω	t _{rr}	4	ns
Forward Recovery Voltage at $I_F = 10$ mA, $t_r = 20$ ns	V _{fr}	1.75	V









SEMTECH ELECTRONICS LTD.

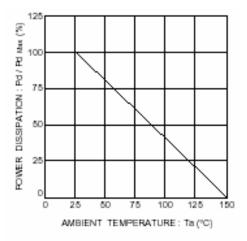


Fig.1 Power attenuation curve

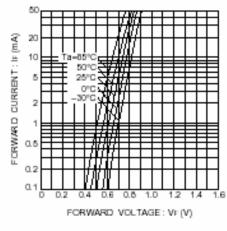


Fig.2 Forward characteristics

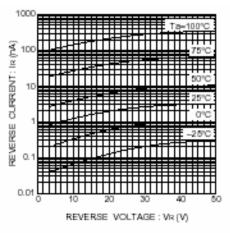


Fig.3 Reverse characteristics

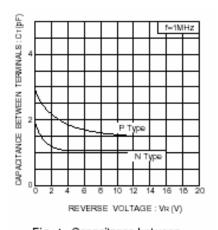


Fig. 4 Capacitance between terminals characteristics

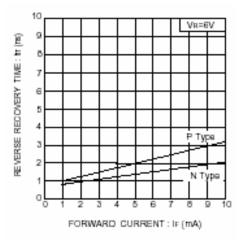


Fig. 5 Reverse recovery time







PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

